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Rad-Hard: From LEO to Deep Space

An update on ST's latest Rad-hard analog, digital and discrete semiconductor components and technologies, with focus on the ST LEO series of Rad-Hard in plastic package and the new Point of Load converter RHRPMPOL01

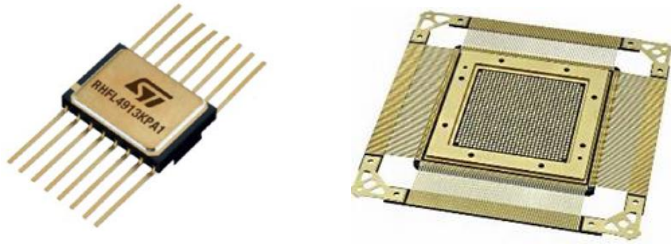
ST Developers' Conference 2021

Piercarlo Scimonelli, Andrew Michel, Thibault BRUNET

State of the art integrated supply chain

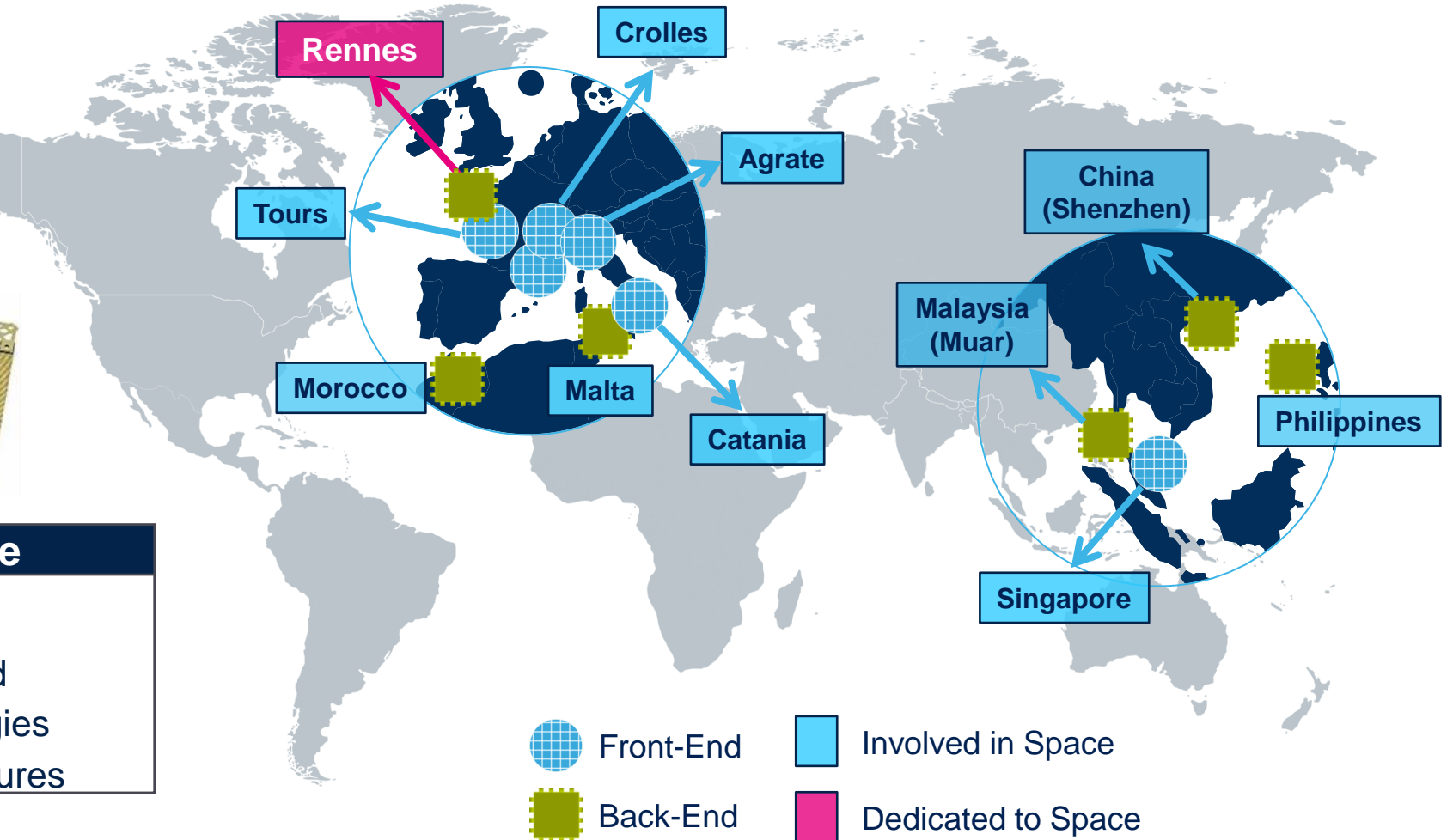


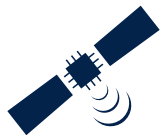
BEM&T Space qualified plant in Rennes



40+ year commitment to Space

- State-of-the-art assembly facility
- QML-V, JANS and ESCC Certified
- Proprietary rad-capable technologies
- Millions of flying hours without failures





A large Rad-Hard product offering

Fast expanding portfolio



Interfaces

LVDS fail safe series
16-bit bus interfaces
Level shifters

Logic

CMOS4000: 100 krad
HCMOS & HCTMOS: 50 krad
AC & ACT MOS: 300 krad

Bipolar & MOSFET transistors

ESCC 100 krad LDR bipolars
JANSR+ 100 krad LDR & VLDR bipolars
Cost effective rad-hard MOSFET

Schottky diodes & Rectifiers

JEDEC D5 compatible series
Power series up to 600 V / 40 A

ASIC technologies & platform

Space platforms:

BCD6s SOI 320nm up to 190V
65nm, 28 nm FDSOI

ST Rad-capable technologies:

CMOS - SiGe 130 & 55 nm
Imaging technologies – Integrated passive RF

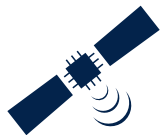
Power management

Linear Voltage regulators
PWM controllers
Gate drivers
Integrated Current Limiter
Point of Load switching converter

Analog

Data converters
Operational Amplifiers and Comparators
Voltage reference





What's new in ST Space offer

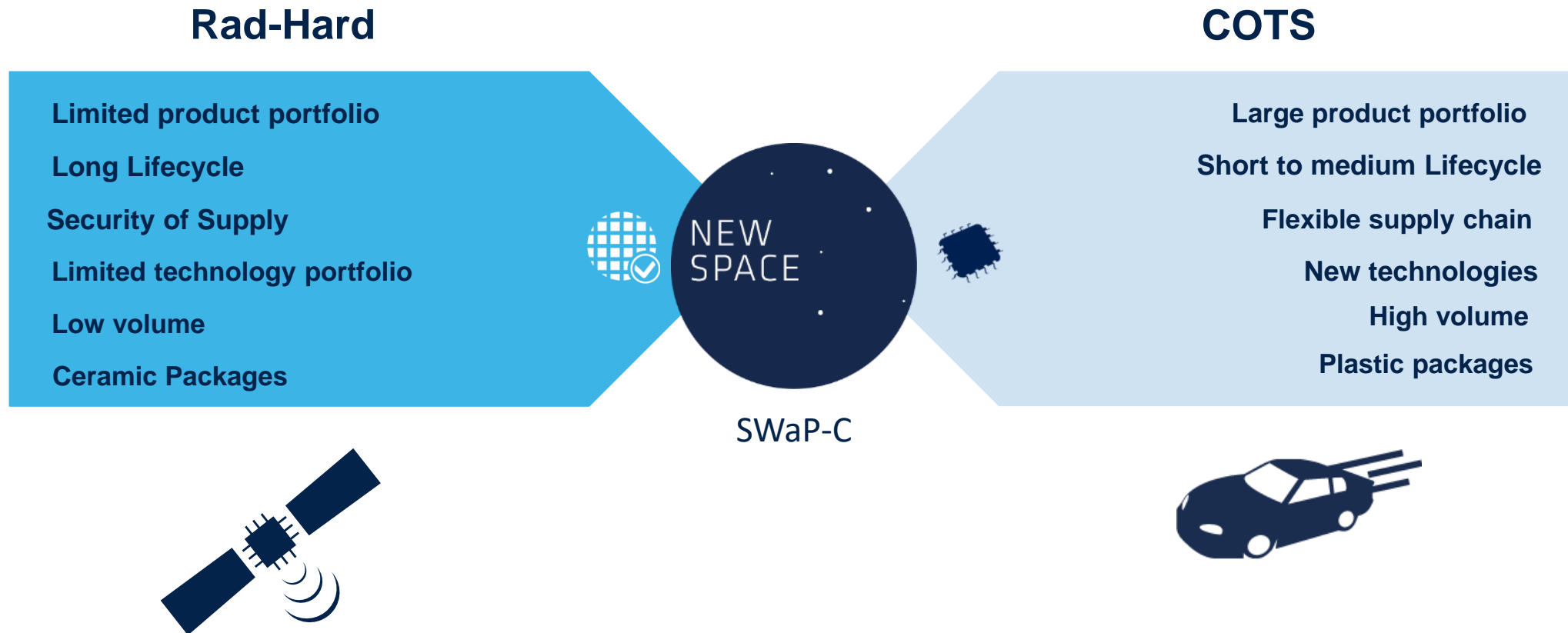
Diodes	STPS series of Rad-Hard Power Schottky from 45 to 150V, up to 80A	ESCC Qualified
Diodes	STTH series of Rad-Hard Power Rectifiers: 200 and 400V up to 80A	ESCC Qualified
Bipolar	2ST15300 High Voltage 300V NPN	ESCC Qualified
Logic	Grounded lid AC & VCX, RHFOSC04 oscillator & clock driver, RHFAHC00 150MHz	QML-V Qualified
D/A Converter	RHRDAC121: 20MHz 12-bit SAR	Eng. Models
A/D Converter	RHFAD128 8-channel 12-bit serial output ADC 1Msps	QML-V Qualified
Current limiter	RHRPMICL1A: Integrated configurable power switch with floating ground	QML-V Qualified
Point of Load	RHRPMPOL01: Fully featured 7A with current sharing and synchronization	QML-V Qualified
LEO series	LEOAD128, LEOAC00, LEOAC14, LEOAC244 and LEOLVDSRD	ST Qualified
Rad-Hard ASIC	65nm: ESCC qualified, 28nm: FD-SOI, Now Flying	Qualified

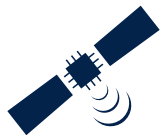


Low Earth Orbit (LEO) Roadmap



The New Space sweet spot





A solution to a new paradigm?

Requirements

Class 1 missions

Low quantity

15 year + lifetime

100 krad(Si) + 85 MeV.cm²/mg

Constellations

Higher quantity

5 to 10 years lifetime

20 to 50 krad(Si) + 40 to 60 MeV.cm²/mg



Solutions

Industry Preferred: agency qualified

- + Fully screened rad-hard ceramic hermetic
- + Known cost of ownership / lead time / risk
- Limited product and performance offer

Alternative: COTS + Upscreen

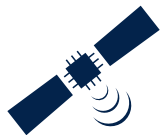
- + Upscreen up to the mission profile
- Higher cost of ownership / lead time / risk
- + Larger product and performance offer

Industry Preferred: plastic rad-hard

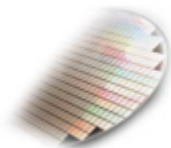
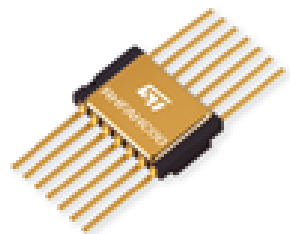
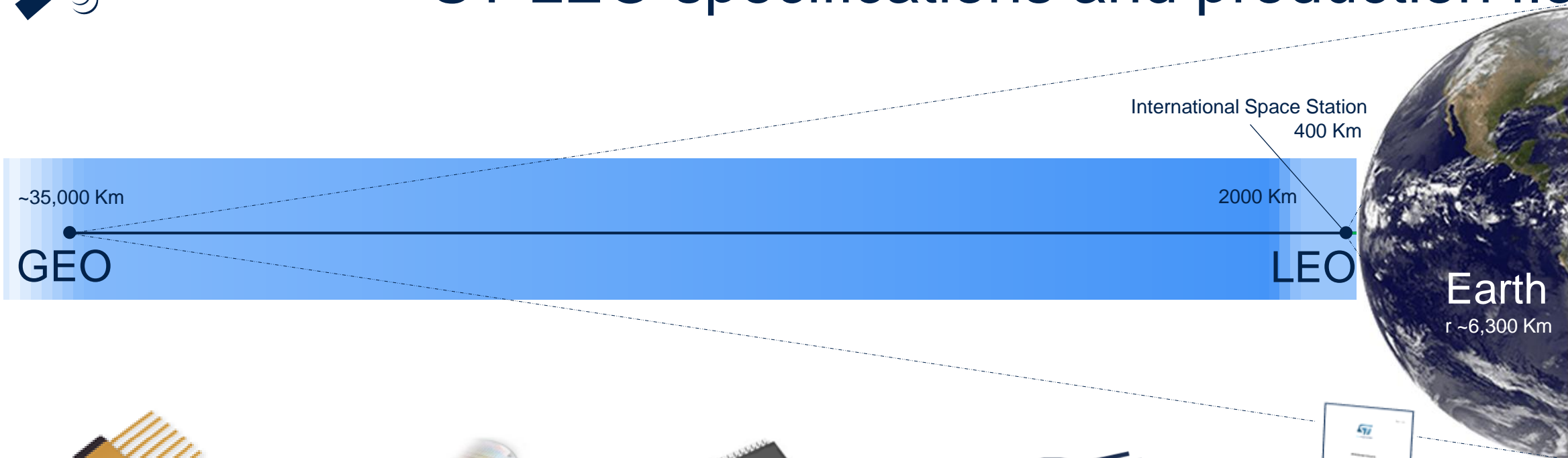
- + Plastic rad-hard with optimized screening
- + Known cost of ownership / lead time / risk
- Limited product and performance offer

Alternative: COTS + upscreen

- + Upscreen up to the mission profile
- Higher cost of ownership / lead time / risk
- + Larger product and performance offer



ST LEO specifications and production flow



Existing Rad-Hard material
in Ceramic package

- 100/300krad(Si) TID
- 120MeV.cm²/mg
- QMLV, ESCC

Dice optimized for
assembly in Plastic
package

Rationalized to

- PSO20 (Power)
- TSSOP20 (Analog)

AECQ-100
production lines
+ Radiation tests

DM00695640
ST-LEO Spec

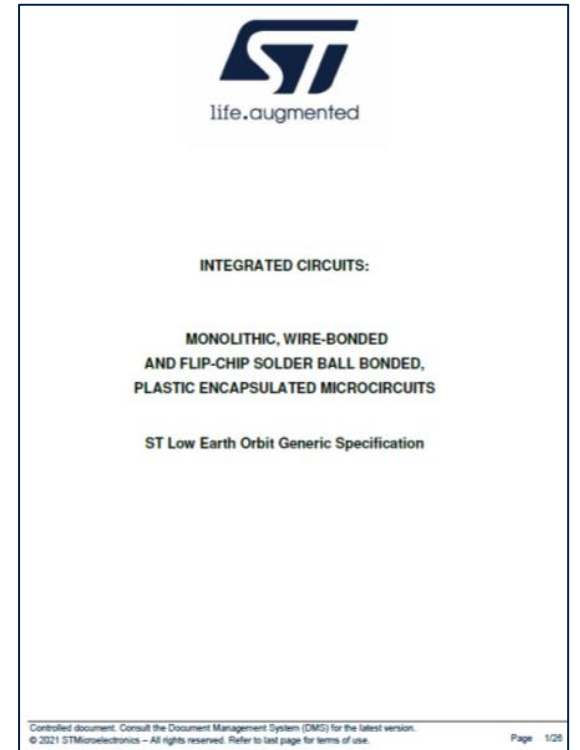
- 50krad(Si) TID
- 43MeV.cm²/mg
- No SLDC
- MOQ up to 1ku



LEO series: Rad-Hard Plastic

AEC-Q100 based

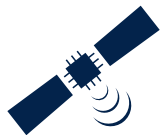
Step	Description
Specification	<p>TID 50krad(Si) – TNID when relevant @ 3.10^{11} proton / cm²</p> <p>SEL free @ 43MeV.cm²/mg minimum + characterization up to 60 MeV.cm²/mg</p> <p>SET / SEU / SEFI... characterized up to 60 MeV.cm²/mg when relevant</p> <p>Operating temperature : -40°C to 125°C with 100% test at Low / Room / High temperature</p> <p>No serialization – No Burn in</p> <p>Certificate of Conformance</p>
Die	<p>Front end with ST Process control</p> <p>Electrical Wafer Sort with PAT⁽¹⁾, GPAT⁽²⁾ and Percentage Defective Acceptance</p> <p>Wafer Lot Acceptance Test : HTOL + TID up to 50krad(Si)</p>
Package	<p>Assembly lines of AEC-Q100 qualified products</p> <p>Default finishing Ni/Pd/Au – Default wires : Gold</p> <p>Molding compound characterization (including RML⁽³⁾ & CVCM⁽⁴⁾)</p> <p>Selected packages : TSSOP20 – PowerSO20; Others under evaluation</p>
Screening	Based on AEC-Q100 : 10 Thermal cycles @ 100% + CSAM by sampling + external visual
Logistic	<p>Packing : Tape & reel</p> <p>MOQ : 1000 pieces typical</p> <p>Max 2 date code per shipment & 1 date code / reel – No additional traceability at order entry</p> <p>Max date code : 5 year</p>
Support	<p>PCN & PTN Management : as ESCC / QML-V</p> <p>Customer services & technical support by ST Space team</p>



**ST LEO specifications
now available**

(1) Part Average Testing; (2) Geographical Part Average Testing

(3) Recovery Mass Loss : target : < 1% (4) Collected Volatile Condensable Material -Target : < 0.1%



LEO series: On-going developments status



Logics



LVDS



ADC



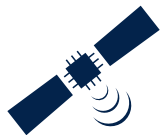
Voltage
regulators

CP	Function	Plastic Package	Sample	Flight Model	Part Number DM / FM
LEOAC00	Quad NAND	TSSOP20	Now	Now	LEOAC00PT-D LEOAC00PT
LEOAC08	Quad AND	TSSOP20	Now	4Q21	LEOAC08PT-D LEOAC08PT
LEOAC14	Hex Schmidt Inverter	TSSOP20	Now	Now	LEOAC10PT-D LEOAC14PT
LEOAC32	Quad OR	TSSOP20	Now	4Q21	LEOAC32PT-D LEOAC32PT
LEOAC74	DUAL Flip / Flop	TSSOP20	Now	4Q21	LEOAC74PT-D LEOAC74PT
LEOAC244	16-bit Transceiver	TSSOP20	Now	Now	LEOAC244PT-D LEOAC244PT
LEOLVDSRD	LVDS Transceiver	TSSOP20	Now	Now	LEOLVDSRDPT-D LEOLVDSRDPT
LEOAD128	8-channel 12-bit ADC	TSSOP20	Now	Now	LEOAD128PT-D LEOAD128PT
LEO3910	LDO	PSO20	Now	4Q21	LEO3910PDT-D LEO3910PDT
LEOPOL1	Switching POL	PSO36	4Q21	1Q22	LEOPOL1PDT-D LEOPOL1PDT



News in Data Converters





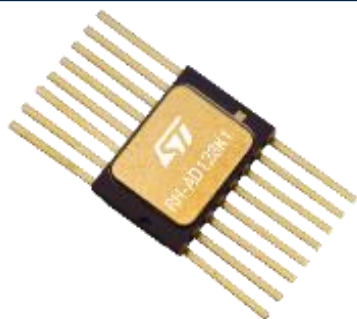
SMD : 5962F18204

RHFAD128

Rad-hard Industry standard 1 Msps 8-channel 12-bit ADC

KEY FEATURES

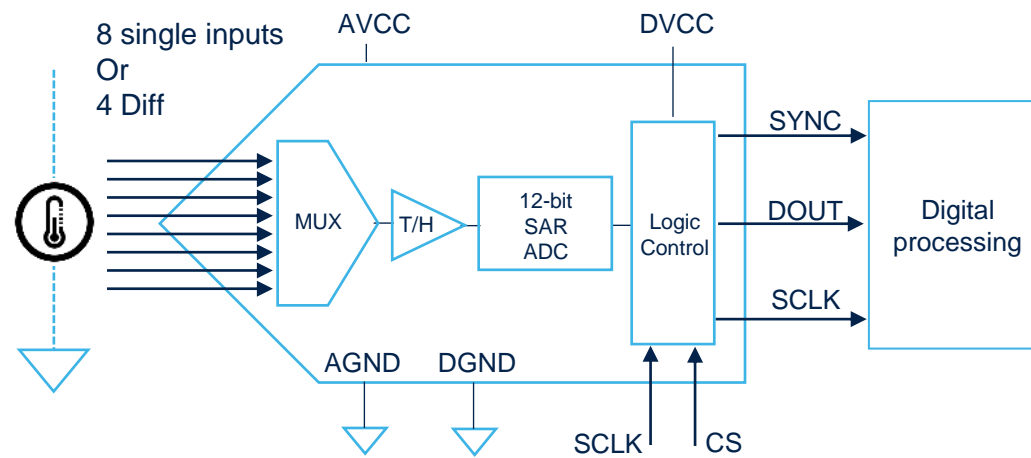
- Industry standard pinout
- No conversion glitch
- SAR architecture
- 12-bit, 50ksps to 1Msps sample rate
- 11.1 ENOB min. over -55/125C
- 4.5mW max @ 3.3V 1Msps, 3μW in shut-down
- 3.3V supply and I/Os
- 8-channel MUX, single-ended input
- 4-channel MUX, diff input
- SPI compatible



Flat-16
Metallic lid
internally grounded

RADIATION HARDENED

- RHA guaranteed at 300 krad(Si) – ELDRS free
- SEL-free up to 125 MeV.cm²/mg @ 125° C
- SEU immune up to 32 MeV.cm²/mg
- SEFI immune up to 62 MeV.cm²/mg



Rad-hard 20MHz low power SAR 12-bit DAC

KEY FEATURES

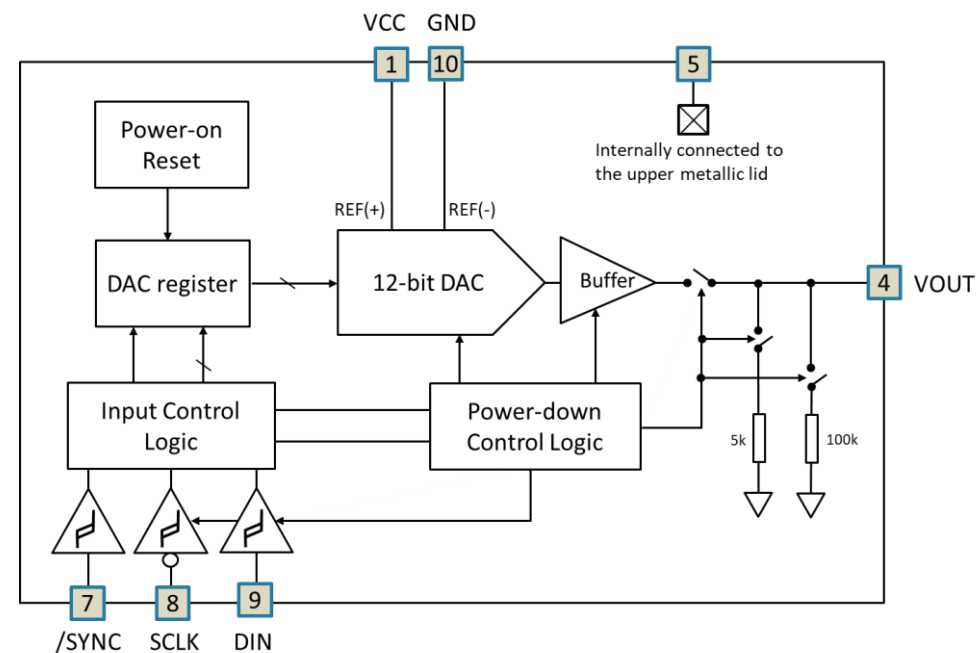
- Industry standard pinout
- 4.8V AMR
- 2.3V to 3.6V Supply Range
- 12-bit SAR architecture
- 180uA consumption at 20MHz clock and Vcc max
- 10mV max offset error
- Rail-to-Rail Voltage Output
- Power-On Reset to Zero Volts Output
- Internal voltage reference
- Series input, SPI compatible
- SYNC Interrupt
- Power-Down Feature



Flat-10
Metal lid
internally grounded

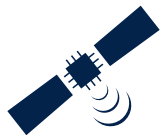
RADIATION HARDENED

- RHA guaranteed at 100 krad(Si)
- SEL-free up to 120 MeV.cm²/mg @ 125C
- SEE report available upon request



News in Logics and Interfaces





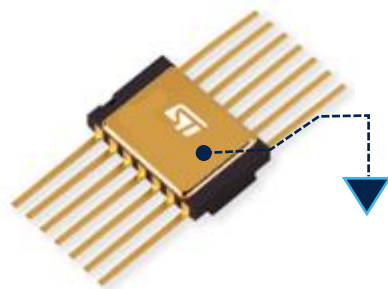
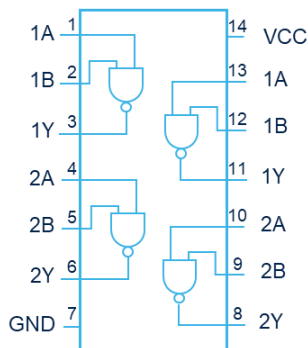
SMD: 5962F18202

RHFAHC00

Rad-hard High speed NAND gate

KEY FEATURES

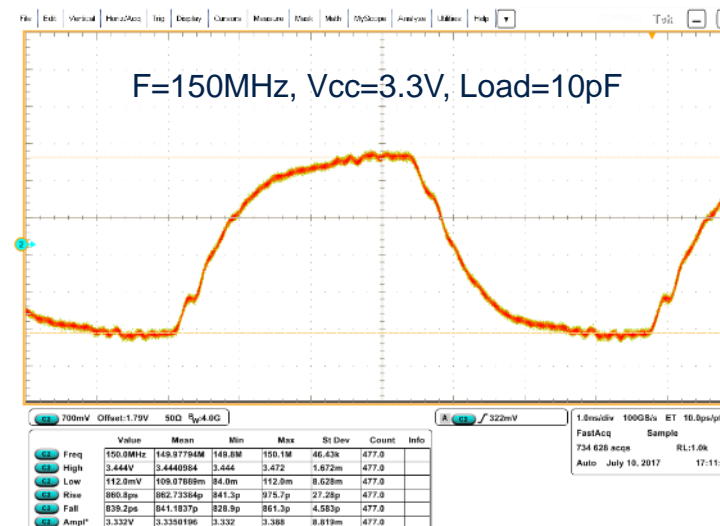
- 1.65V to 3.6V operating supply
- 4.8 V AMR
- Ultra low power
- 50 μ A quiescent current (no load)
- 165 μ W at 3.3V
- Very high speed
- propagation delay of 3 ns max.
- Functionally tested at 150MHz
- FLAT14 with grounded lid



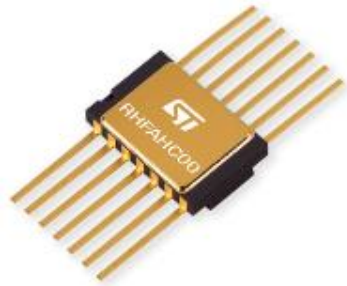
Grounded Lid:
AC/VCX Internal connection of the
metallic lid to a pin for grounding

RADIATION HARDENED

- 300 krad (Si)
- SEL free up to 125 MeV.cm²/mg @ 125C
- SET free up to 62.5 MeV.cm²/mg @ 25C
- Proven CMOS 130nm technology



AC00 vs. AHC00



	5962F87549	5962F18202
	54AC00	RHF54AHC00
Supply	Nominal 2.5V 3.3V 5V Tested from 3 to 5.5V	Nominal 1.8V 2.5V 3.3V Tested from 1.65 to 3.6V
Max Freq	70MHz max (char)	+150MHz (char)
Prop time	9ns	3ns
Output level @3V	VOH=2.9V for IOH=50uA	VOH=2.8V for IOH=100uA
Radiation	300 krad(Si) TID 110 MeV.cm2/mg SEL free 85 MeV.cm2/mg SET free	300 krad(Si) TID 125 MeV.cm2/mg SEL free 62.5 MeV.cm2/mg SET free
Tech	700nm	130nm
In production	yes	yes



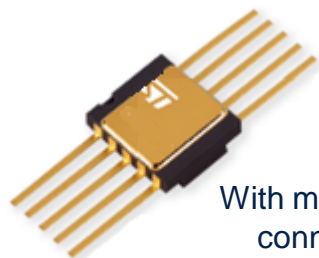
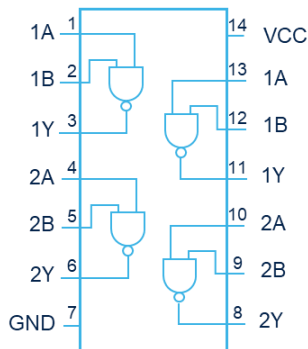
SMD: 5962F20207

RHFOSC04

Rad-hard Crystal oscillator driver/divider

KEY FEATURES

- 1.8V 2.5V 3.3V logics compatible, 4.8V AMR
- 4 selected frequency-divided outputs
- 16MHz-120MHz Crystal range
- 18pF output capability
- -100dBc Phase-Noise at 170Hz@120MHz
- 3.4mA current consumption
- Enable/Disable with high-impedance output
- Dice: 1mm², 10-pads, 100x100µm
- Flat10 hermetic package
- HCMOS9A (130nm CMOS technology)



Flat-10

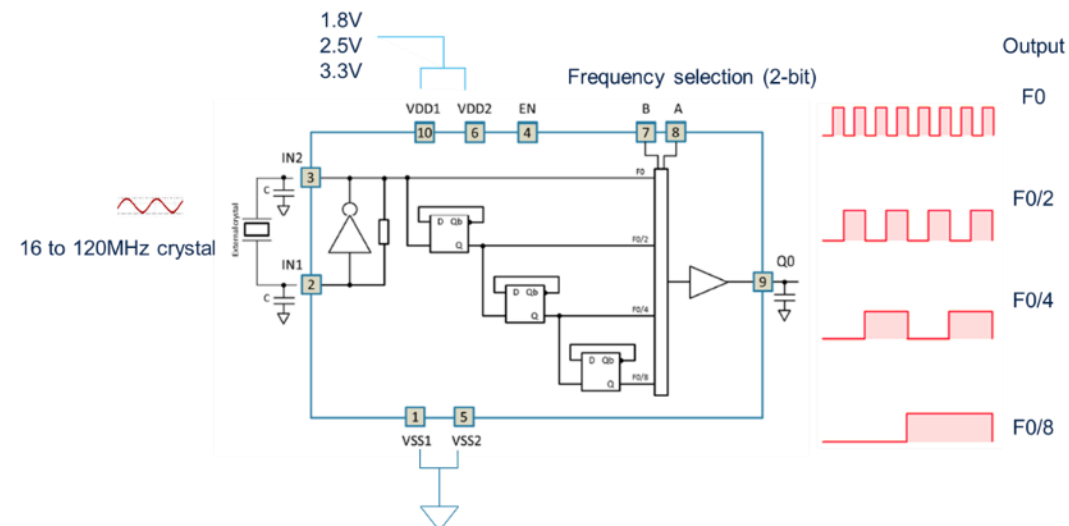
With metallic lid internally connected to ground



Die form

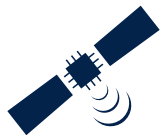
RADIATION HARDENED

- 300 Krad (Si)
- SEL free @ 120 MeV.cm²/mg @ 125C
- SET: Report available upon request
- Proven 130nm technology



News in Power Management





SMD : 5962R17211

RHRPMICL1A

Rad-Hard Integrated Current Limiter

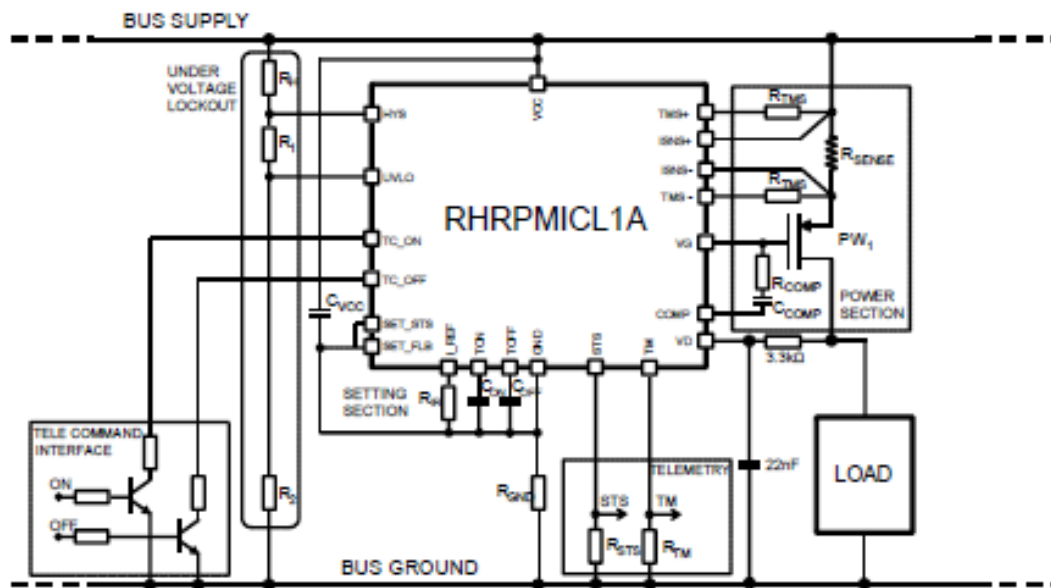
MAIN BENEFITS & FEATURES

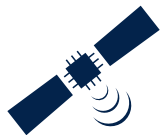
- **Wide-range supply voltage: 8.5 – 52V DC**
- **Floating Ground functionality for >52V operation**
- Very Low DC current: typ 1.5 mA (2mA in Floating Ground)
- 3 Operation Modes
 - Re-Triggerable
 - Latched
 - Fold-back
- High Configurability
 - External current limit setting
 - Configurable trip-off and recovery times
 - Under-voltage thresholds (ON and hysteresis)
- Digital & Analog telemetries
- Flat-20 Hermetic Package



RADIATION HARDENED

- TID: 100 krad (Si) ELDRS free
- SEL & SEU free up to 125 MeV.cm²/mg
- SET characterized





SMD: 5962R20208

RHRPMPOL01

Rad-Hard Point of Load 7A monolithic step-down regulator

KEY FEATURES

- Input operating voltage range: 3.0V to 12V
- Output voltage range: 0.8V to 0.85xVin
- Fast load transient response Peak Current Mode control loop
- Integrated NCH MOSFETs for synchronous step-down conversion
- Integrated BOOT diode
- Fully protected:
 - Under & over voltage
 - Over temperature
 - 2 level over current protection
- Power good output
- Programmable switching frequency from 100kHz to 1MHz
- Easy smart out-of-phase synchronization of multiple devices⁽¹⁾
- Current sharing configuration for higher load requirements
- Programmable soft-start

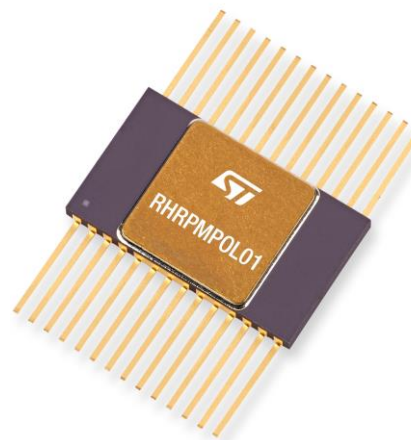
(1) No external components for 180° out of phase of 2 devices



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RADIATION HARDNESS

- Total Ionizing Dose: 100 krad
- Tested ELDRS-free
- SEL-free up to 70 MeV/mg/cm² @ Vcc up to 7V
- SEU-SEFI characterized up to Vcc 7V - Proton Free
- No performance degradation due to SET



Flat-28A



Die form



SMD: 5962R20208

RHRPMPOL01

Application Tips

Synchronization for 180° out of phase dual output or Interleaving

Master mode

The device is automatically configured as Master **when pin FSW is > 0.15V**.
The pin SYNC, configured as output, provides a clock signal phase-shifted by 180° with respect to the internal clock signal.
It can be used to drive the pin SYNC of another RHRPMPOL01 configured as SLAVE

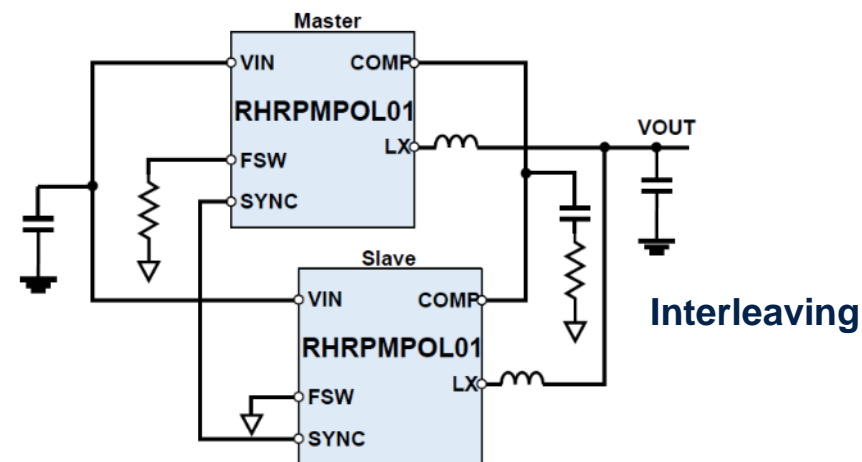
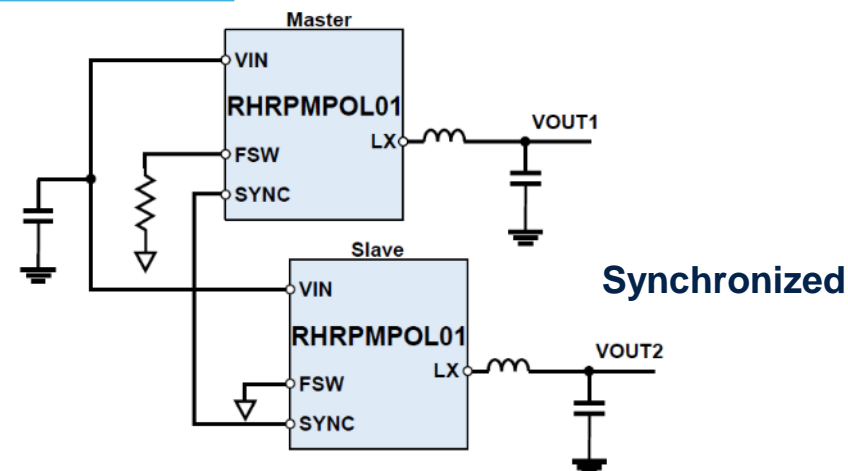
Slave mode

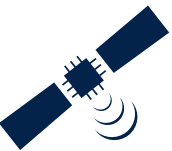
The device is configured as Slave **when pin FSW is forced < 0.1V**.
The SYNC pin, configured as input, accepts a clock signal which can come either from another RHRPMPOL01 configured as master or an external clock.
If an external clock is available, then two RHRPMPOL01 configured as Slave can work in parallel.

Interleaving & Current Sharing

Connecting two RHRPMPOL01s through the SYNC pin, they can synchronize each other with 180° phase shift switching interleaving, reducing RMS current absorption from the input filter and preventing beating frequency noise, therefore allowing a reduction in the size and cost of the input filter.

For **higher output current requirements**, two RHRPMPOL01s can be connected in current share configuration, and providing up to 14A.



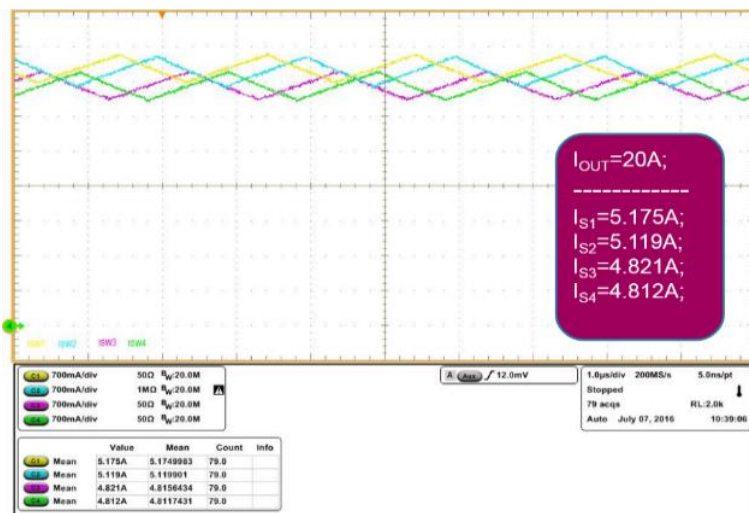
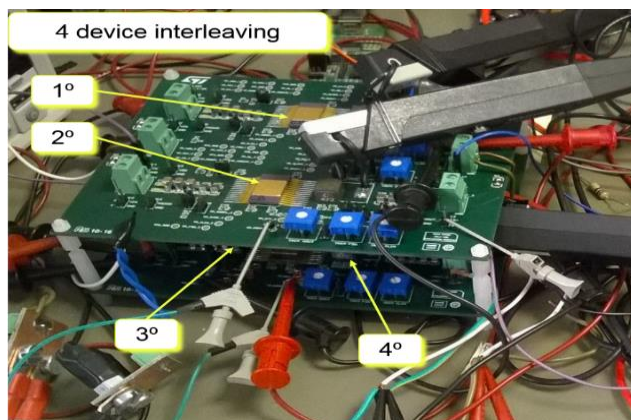


SMD: 5962R20208

RHRPMPOL01

Application Tips

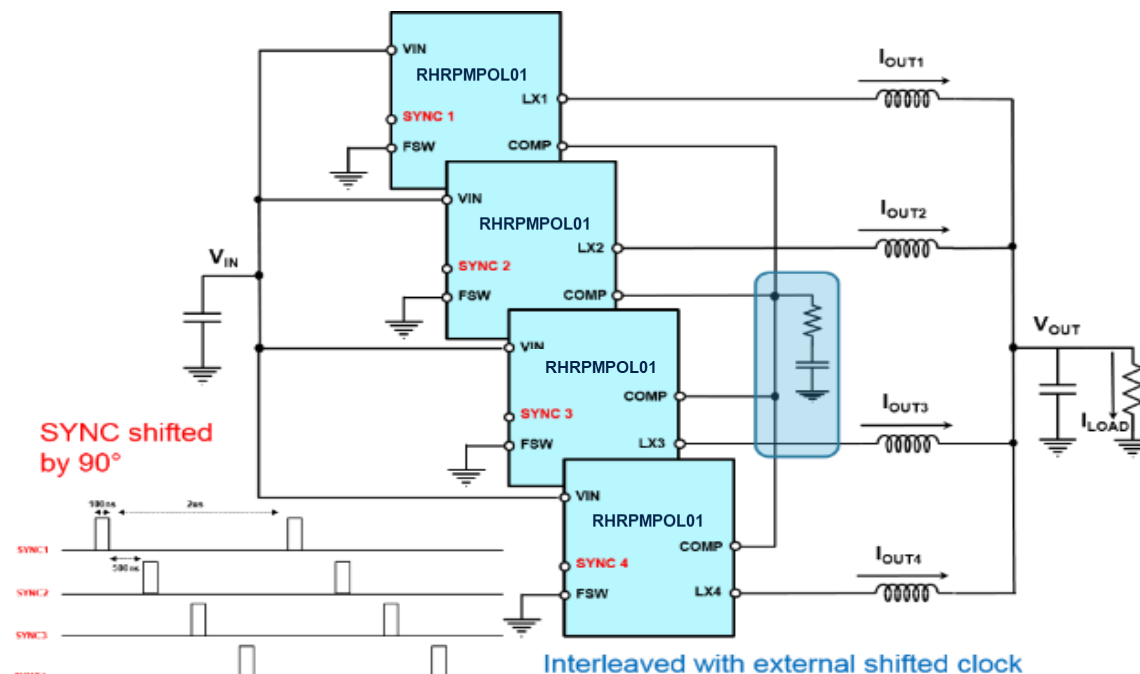
Interleaving 4 devices

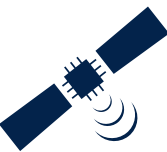


Master and Slave (4 devices) single output:

To guarantee the right phase shifting **each device works as slave** and an external circuit provides the 90° phase shifted SYNC signal:

$$0.9 * \frac{I_{LOAD}}{4} < I_{COIL(1,2,3,4)} < 1.1 * \frac{I_{LOAD}}{4}$$





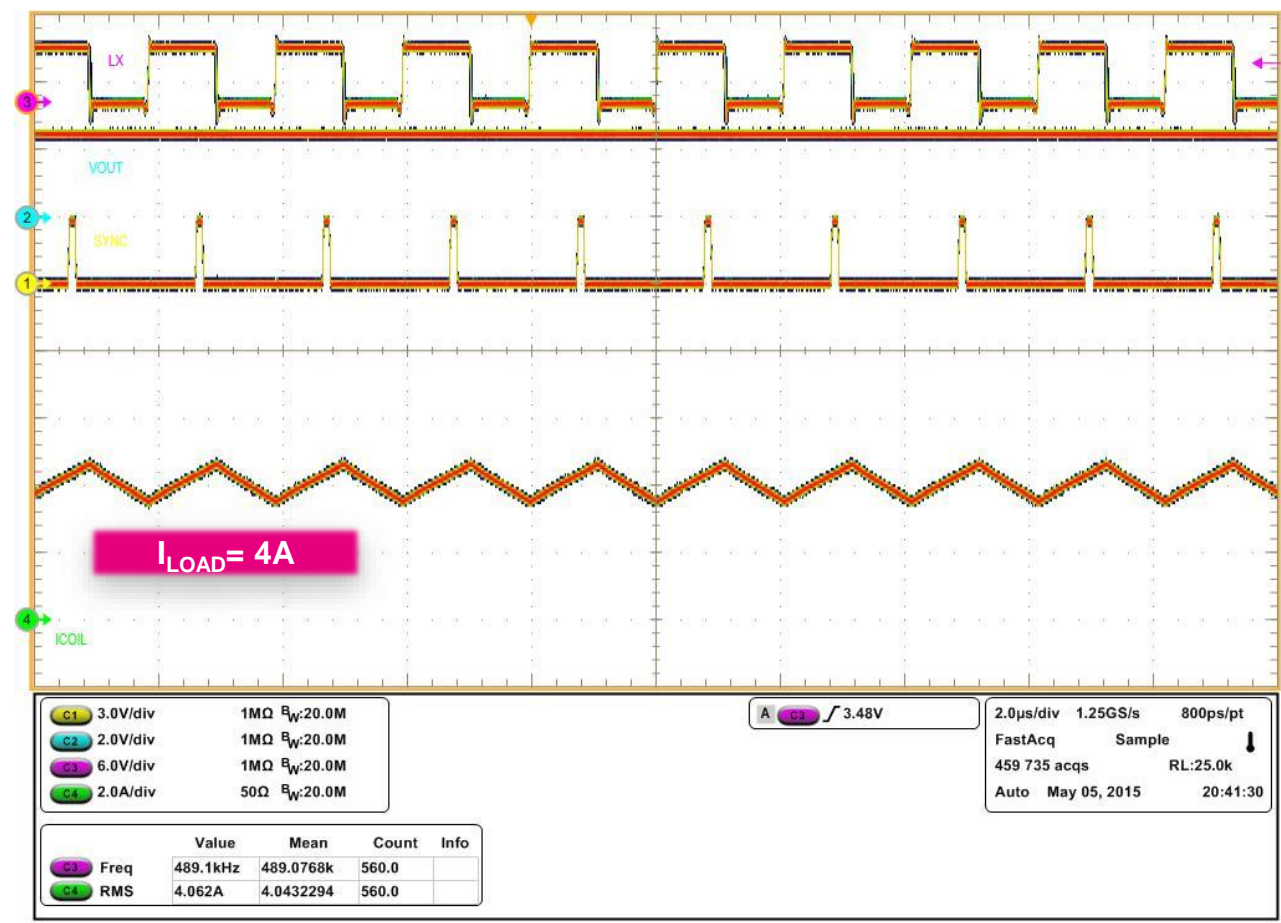
SMD: 5962R20208

RHRPMPOL01

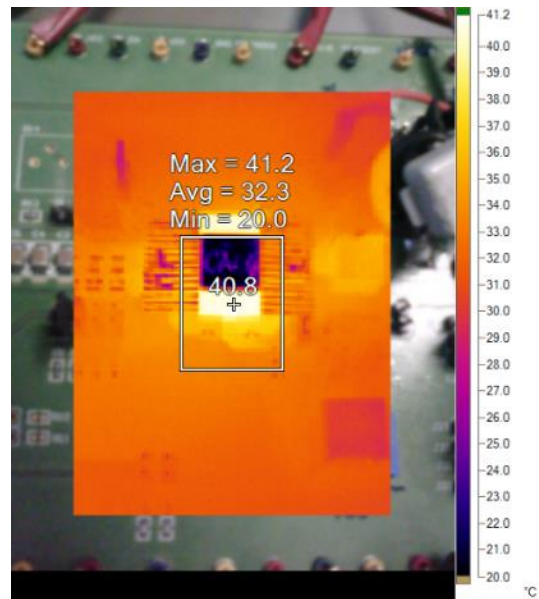
Application Tips

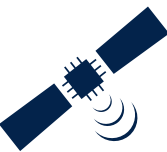
Current Capability

1/3



- $V_{IN} = 5V$
- $V_{OUT} = 2.5V$
- $COIL = 2.2\mu H$
- $FREQ = 500kHz$
- $I_{LOAD} = 4A$
- $EFF = 89\%$
- $P_{DISS} = 1.27W$
- Pack Temp = 41°C





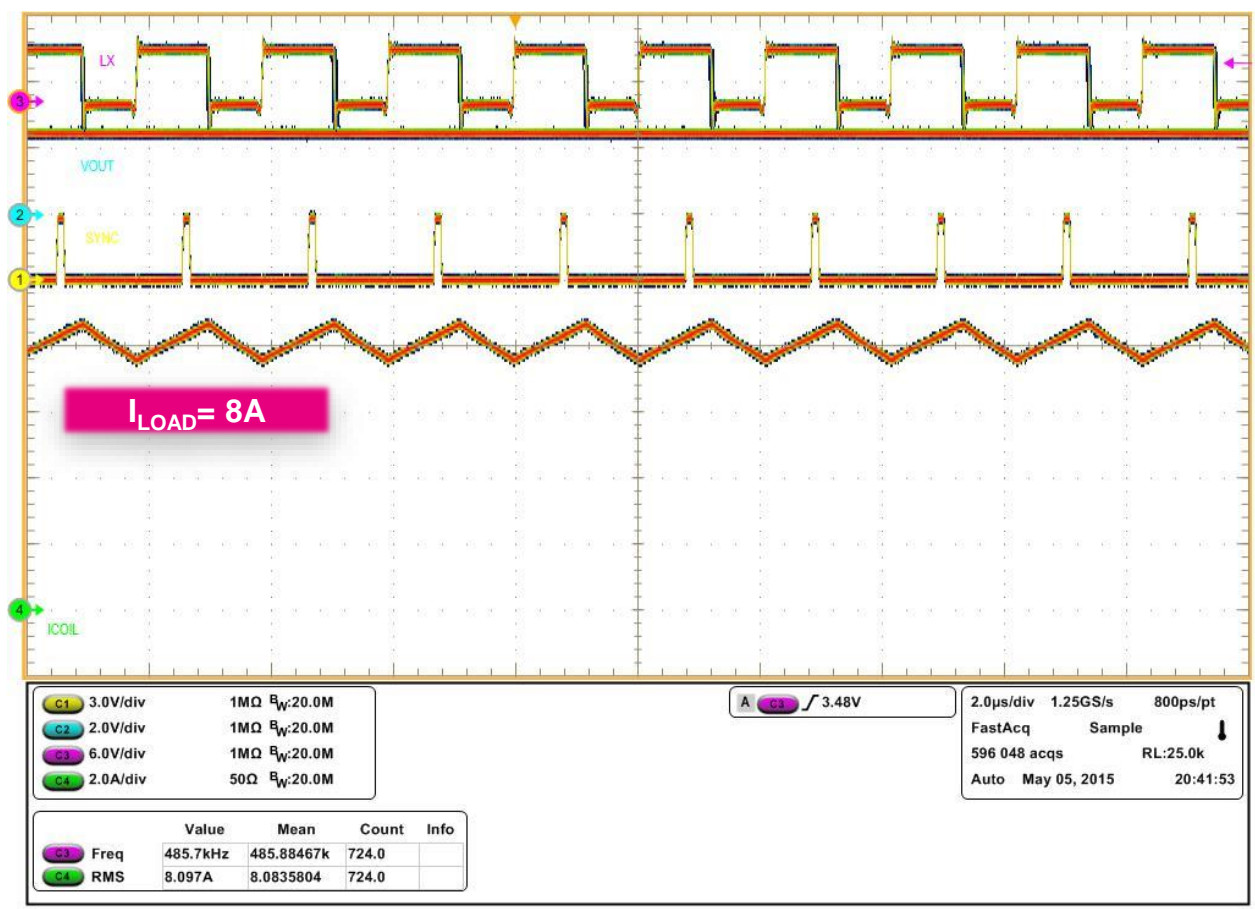
SMD: 5962R20208

RHRPMPOL01

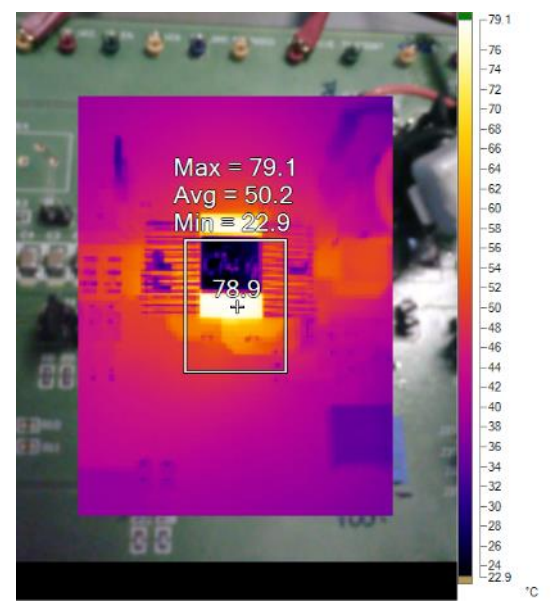
Application Tips

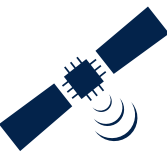
Current Capability

2/3



- $V_{IN} = 5V$
- $V_{OUT} = 2.5V$
- $COIL = 2.2\mu H$
- $FREQ = 500kHz$
- $I_{LOAD} = 8A$
- $EFF = 83.2\%$
- $P_{DISS} = 4.06W$
- Pack Temp = 79°C



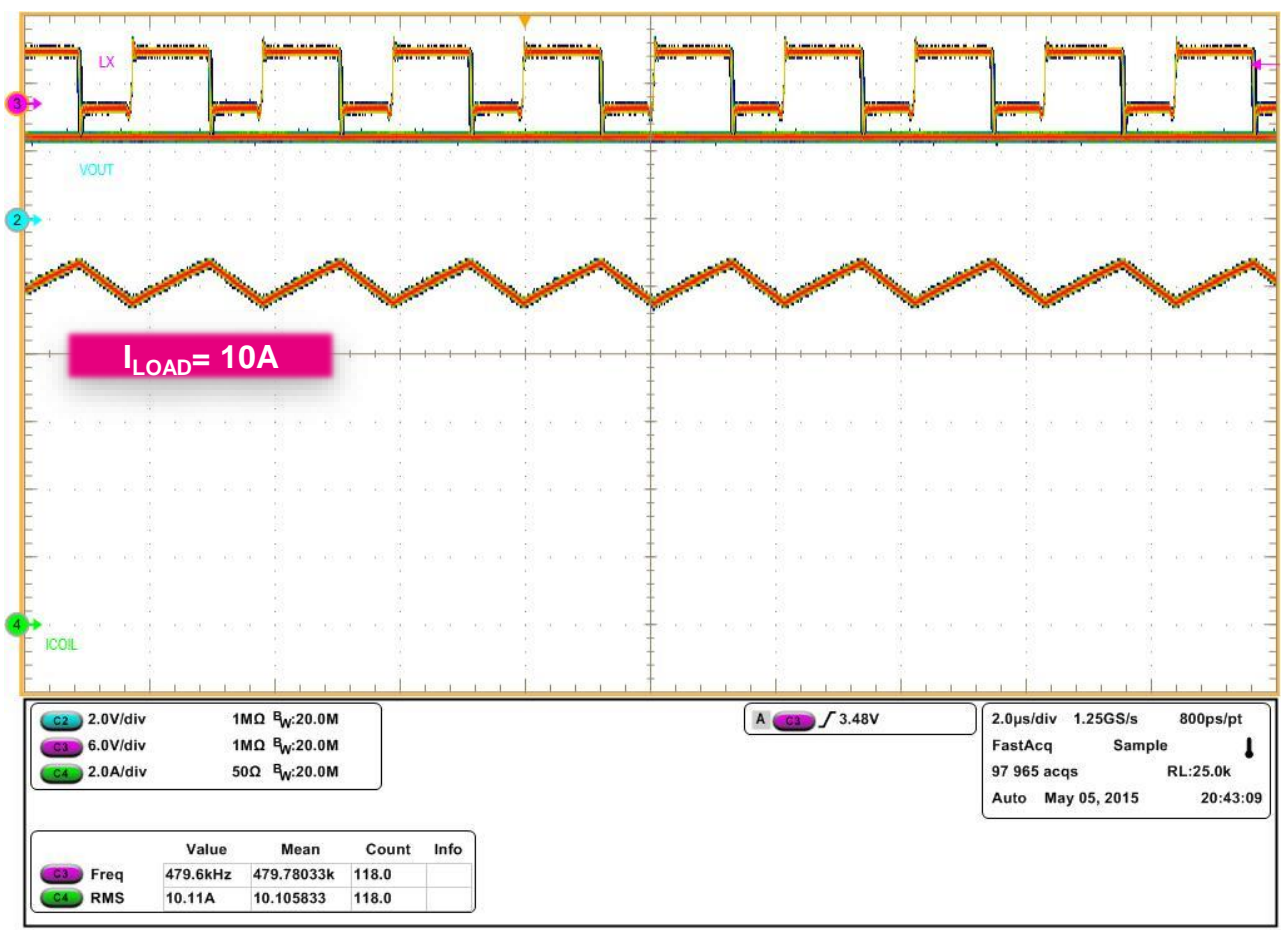


SMD: 5962R20208

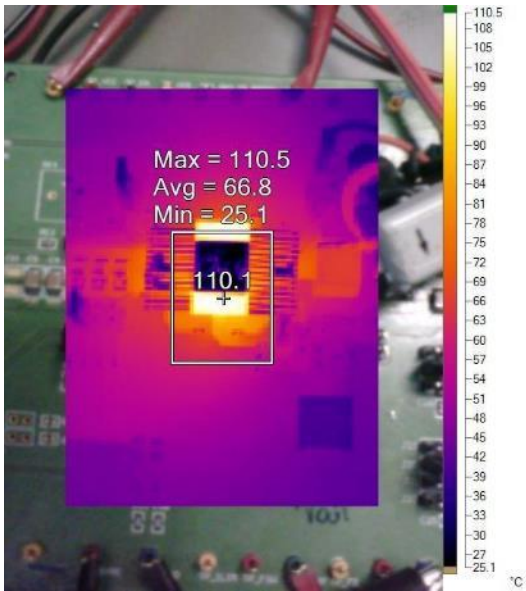
RHRPMPOL01

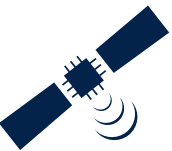
Application Tips

Current Capability 3/3



- V_{IN} = 5V
- V_{OUT} = 2.5V
- COIL = 2.2μH
- FREQ = 500kHz
- I_{LOAD} = 10A
- EFF = 80%
- P_{DISS} = 6.32W
- Pack Temp = 110°C





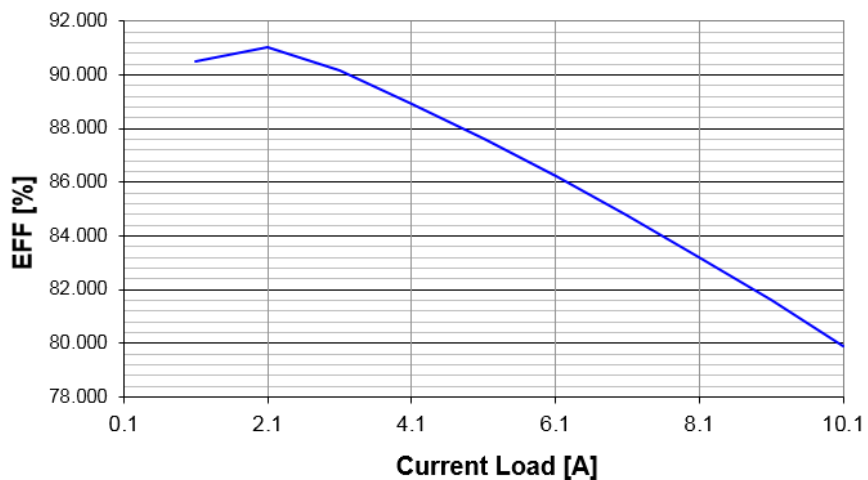
SMD: 5962R20208

RHRPMPOL01

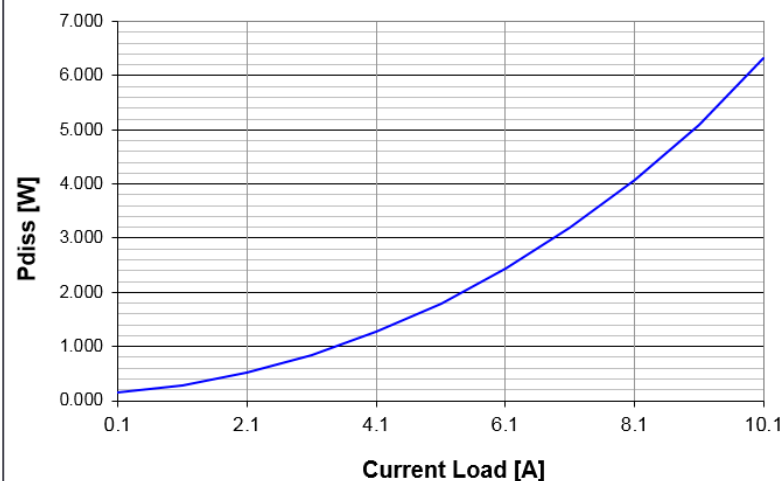
Application Tips

Efficiency, Power Dissipation & Load Regulation

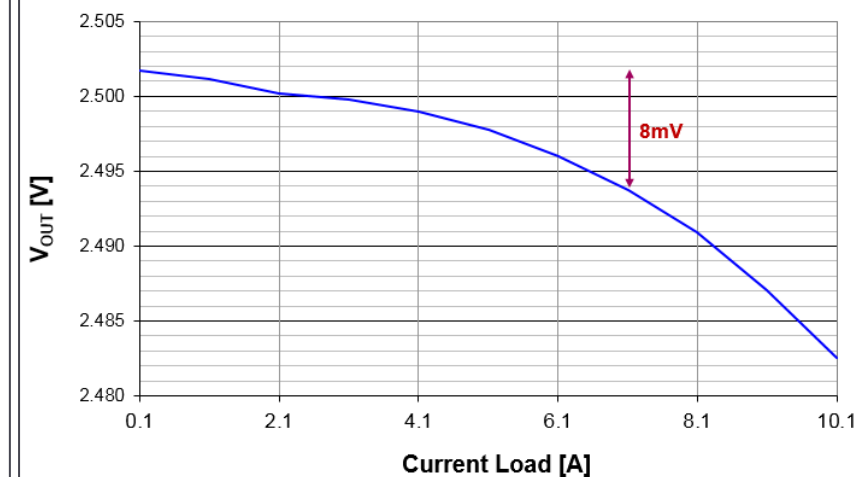
Efficiency



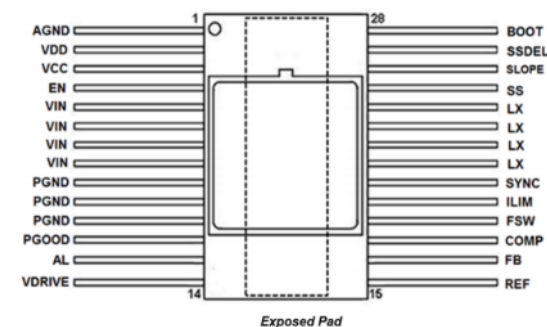
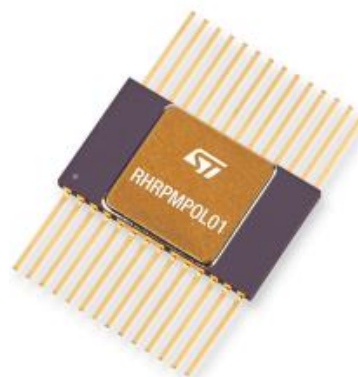
Power Dissipation

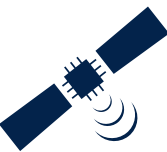


Load Line Regulation

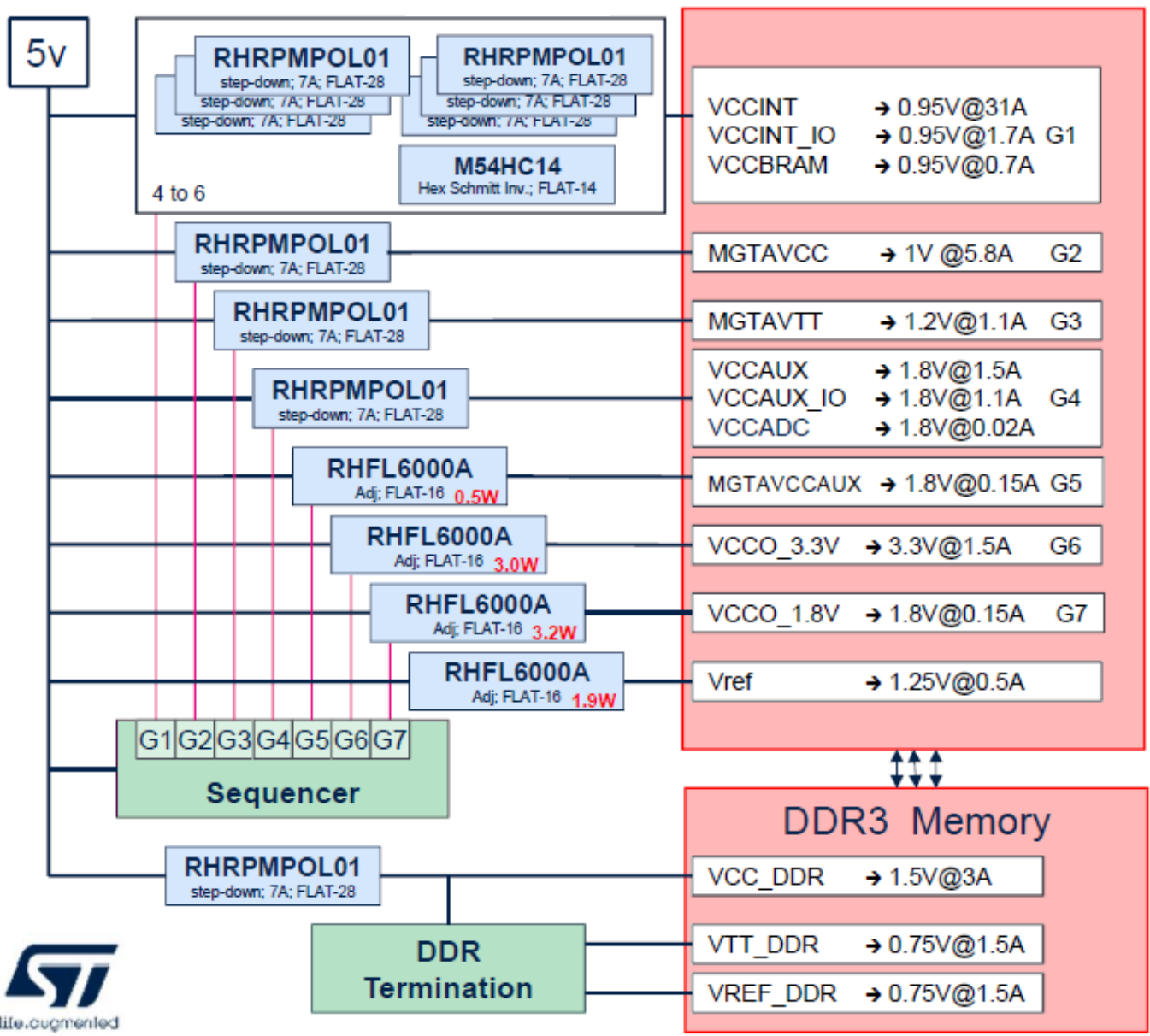


- $V_{IN} = 5V$
- $V_{OUT} = 2. V$
- $COIL = 2.2\mu H$
- $FREQ = 50 kHz$
- $I_{LOAD} = 1A \div 10A$



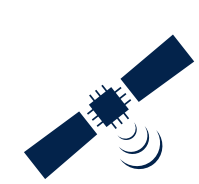


KU060 FPGA Power Reference Design



Foundry & ASICs





High-End Space Foundry & ASICs

ST Integrated Solutions

Technologies for Space

28nm FDSOI: Flying

- 3 rad-Hard platforms - 5 mission profiles

Space 65nm: Development

- Rad-Hard platform - GEO mission profile

BiCMOS55: Development

- SiGe 55nm – FT 330 MHz
- Rad-capable

BiCMOS9: Flying

- SiGe 130nm – FT 220 MHz
- Rad-capable

BCD6s SOI: Flying

- 320nm Up to 190 volt
- Basic Rad-Hard library & IPs

Hardening Expertise

30+ years experience

- 1000s rad tests on many cells & chips
- Several technologies down to 7nm

Proprietary Tools & Methods

- Radiation sensors
- TID-aware aging models
- Multi-scale fault injection simulator
- SEU Montecarlo code
- Ultra-selective hardening (CPU, SOC)

Rad-Hard IPs & Libraries⁽¹⁾

- SERDES, ADC, DAC, PLL...
- ARM : A53, R52 rad-hard macrocells

Integrated Supply Chain

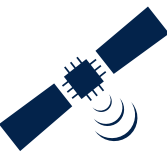
QML-V RHA - ESCC - JANSR

Upgraded Space BEM&T Plant

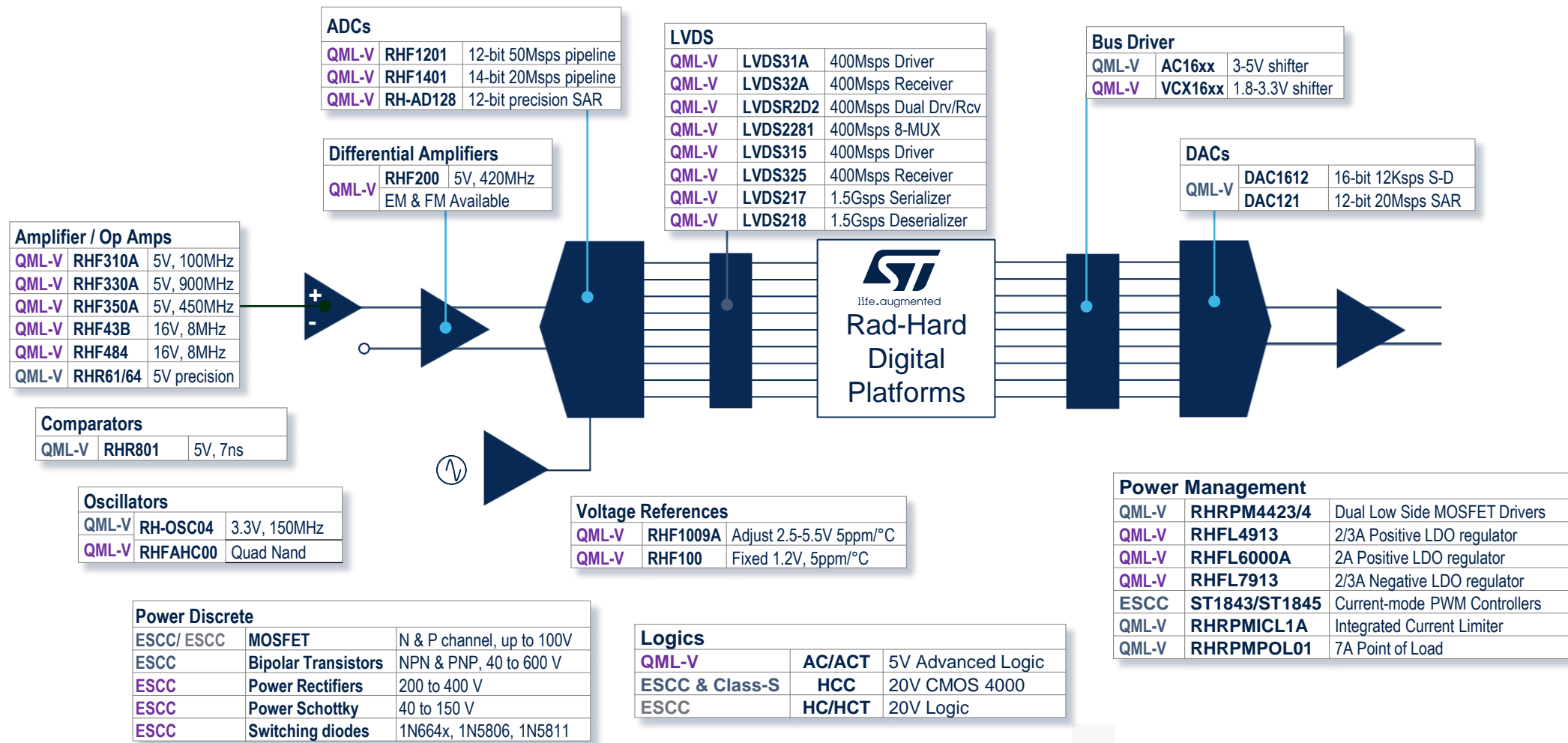
Large Package Offer

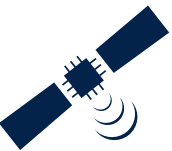
- Ceramic wire-bonded up to 625 pins
- Ceramic flip-chip up to CCGA-1752
- Plastic for Space
- Flip-chip organic substrate

(1) Deployed for Space in 65 nm and 28 nm FDSOI



QML-V and ESCC Reference blocks





Takeaways

- 5 LEO Rad-hard plastic products are ST qualified
- New RHRDAC121 Rad-Hard industry standard 12-bit DAC available
- New 7A Point of Load switcher RHRPMPOL now available
- ST opens its portfolio of rad-capable technology and state of the art supply chain for Space ASICs and ASSPs
- Stable lead times

Our technology starts with You

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